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NTE605A Silicon Varistor Temperature Compensating Diode DO-35 Type Package

Features:

- High Reliability Planar Chip and Glass Sealing
- Low I_R
- Large P_D

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Maximum Forward Current, I_{FM}	100mA
Reverse Voltage, V_R	6V
Power Dissipation, P_D	150mW
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 6\text{V}$	-	-	1	μA
Forward Voltage	V_F	$I_F = 1.5\text{mA}$	0.77	-	-	V
		$I_F = 3\text{mA}$	1.26	-	1.36	V
Forward Voltage Change with Respect to Temperature	$-\Delta V_F/\Delta T$	$I_F = 3\text{mA}$	-	4.6	-	$\text{mV}/^\circ\text{C}$

